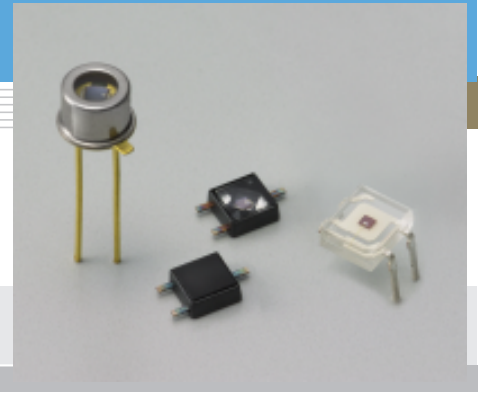


GaAsP photodiode

Diffusion type

Short-wavelength type photodiode



Features

- Low dark current
- Narrow spectral response range

Applications

- Analytical instruments
- UV detection

■ General ratings / Absolute maximum ratings

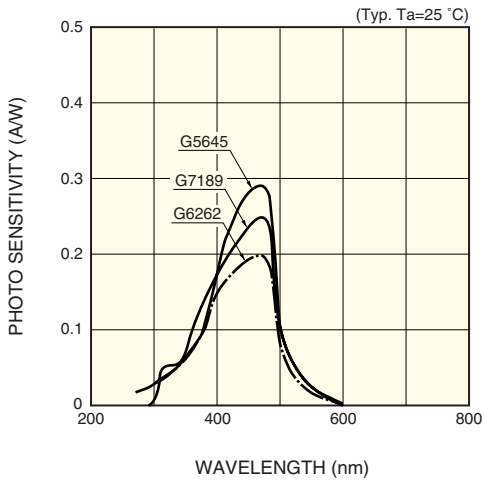
Type No.	Dimensional outline/ Window material *	Package	Active area size (mm)	Effective active area (mm ²)	Absolute maximum ratings		
					Reverse voltage V _R Max. (V)	Operating temperature T _{opr} (°C)	Storage temperature T _{stg} (°C)
G5645	①/K	TO-18	0.8 × 0.8	0.58	5	-30 to +80	-40 to +85
G5842	②	Plastic					
G6262	②	Plastic					
G7189	③/R	Plastic					

■ Electrical and optical characteristics (Typ. T_a=25 °C, unless otherwise noted)

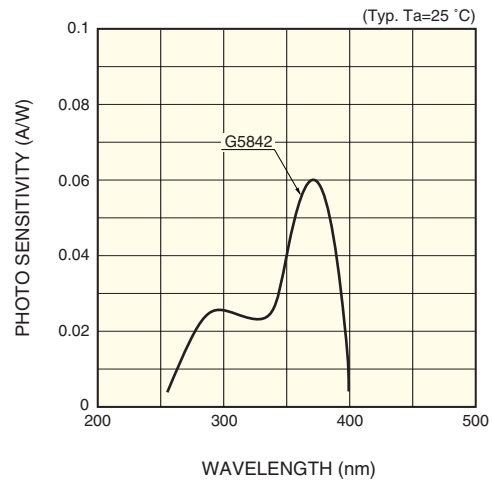
Type No.	Spectral response range λ (nm)	Peak sensitivity wavelength λ _p (nm)	Photo sensitivity S (A/W)		Short circuit current I _{sc} 1000 lx		Dark current I _D V _R =5 V Max. (pA)	Temp. coefficient of I _D T _{CID} (times/°C)	Rise time t _f V _R =0 V R _L =1 kΩ (μs)	Terminal capacitance C _t V _R =0 V f=10 kHz (pF)	Shunt resistance R _{sh} V _R =10 mV		NEP (W/Hz ^{1/2})
			λ _p	GaP LED 560 nm	Min. (nA)	Typ. (nA)					Min. (GΩ)	Typ. (GΩ)	
G5645	300 to 580	470	0.28	0.05	60	90	50	1.07	3	80	10	80	2.3 × 10 ⁻¹⁵
G5842	260 to 400	370	0.06	-	-	2							7.6 × 10 ⁻¹⁵
G6262	280 to 580	470	0.2	0.05	45	65							2.3 × 10 ⁻¹⁵
G7189	300 to 580	470	0.25	0.02	45	65							2.3 × 10 ⁻¹⁵

* Window material K: borosilicate glass, R: resin coating

■ Spectral response

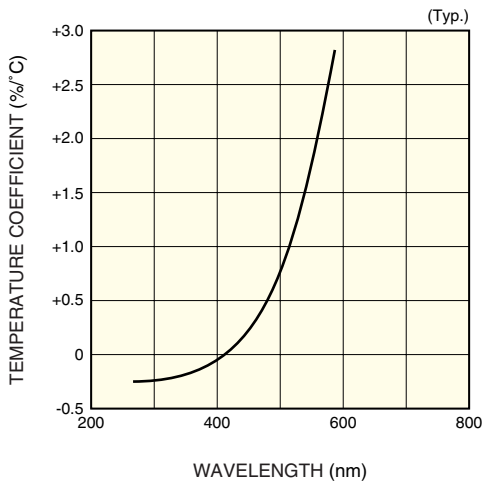


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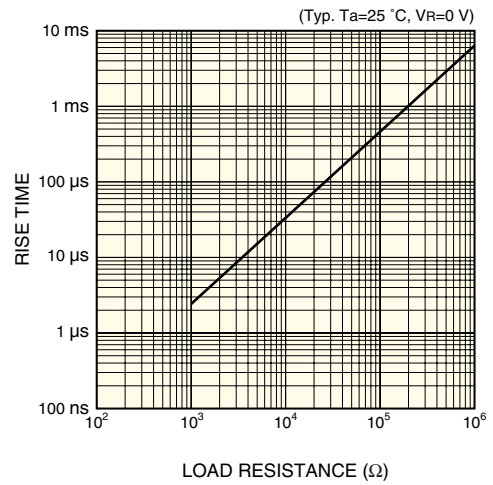
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■ Photo sensitivity temperature characteristic



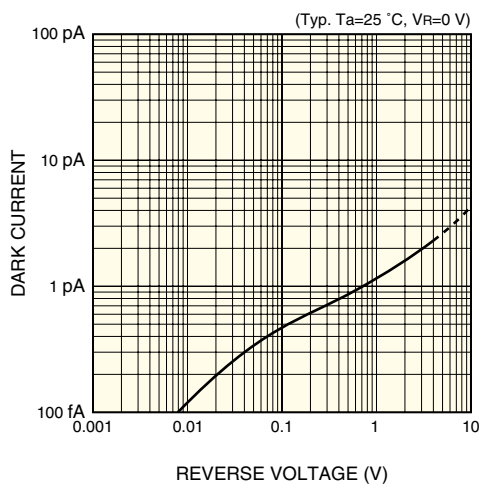
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■ Rise time vs. load resistance



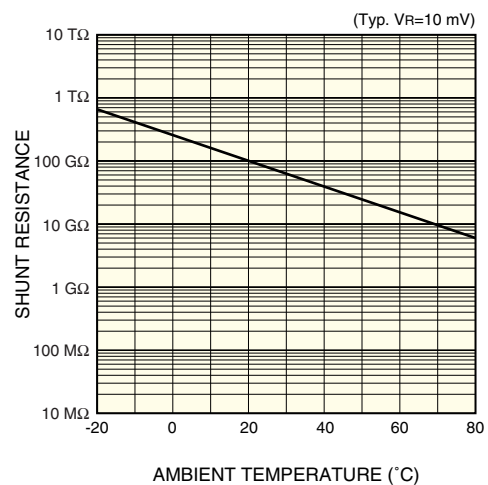
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■ Dark current vs. reverse voltage



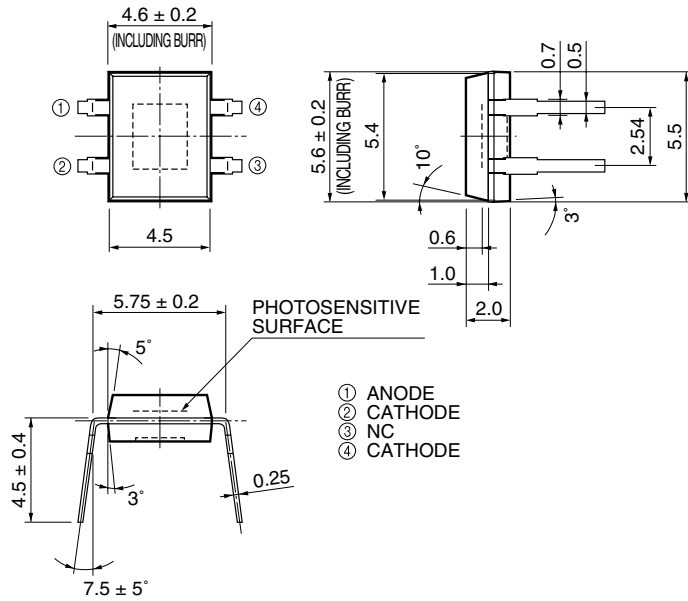
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■ Shunt resistance vs. ambient temperature



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③ G7189



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